ABSTRACT

A method for producing a silicon ingot through pulling up a silicon single crystal according to the Czochralski method, wherein the silicon single crystal is pulled up while being doped with nitrogen in such a condition as to form a part having a nitrogen content of 5×10^{13} atoms/cm^3 to 1×10^{15} atoms/cm^3. A silicon wafer having a nitrogen content of 5×10^{13} atoms/cm^3 to 1×10^{15} atoms/cm^3 which is suitable for being treated with heat in a non-oxidizing atmosphere is manufactured of an ingot produced by using the method. The method can be used for producing a silicon wafer being doped with nitrogen and having satisfactory characteristics for use in a semiconductor device.